TECHNICAL DATA DATA SHEET 650, REV. B

# HERMETIC POWER SCHOTTKY RECTIFIER Very Low Voltage Drop

DESCRIPTION: A 45 VOLT, 7.5 AMP, POWER SCHOTTKY RECTIFIER IN A SHD-1/1B PACKAGE.

## **MAXIMUM RATINGS**

ALL RATINGS ARE @  $T_C = 25$  °C UNLESS OTHERWISE SPECIFIED.

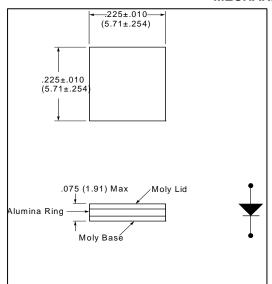
RATING / CONDITION	SYMBOL	MAX.	UNITS
PEAK INVERSE VOLTAGE	PIV	45	Volts
MAXIMUM DC OUTPUT CURRENT (With Cathode Maintained @ T <sub>C</sub> =100 <sup>O</sup> C)	Io	7.5	Amps
MAXIMUM NONREPETITIVE FORWARD SURGE CURRENT	I <sub>FSM</sub>	140	Amps
(t=8.3ms, Sine)			
MAXIMUM JUNCTION CAPACITANCE (V <sub>r</sub> =5V)	C <sub>T</sub>	400	pF
MAXIMUM THERMAL RESISTANCE (Junction to Mounting Surface, Cathode)	$R_{ heta JC}$	3.2	°C/W
MAXIMUM OPERATING AND STORAGE TEMPERATURE RANGE	Top/Tstg	-65 to + 150	°C

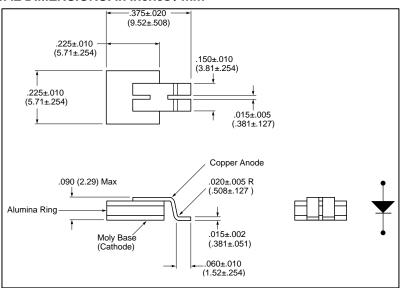
#### **ELECTRICAL CHARACTERISTICS**

CHARACTERISTIC				
MAXIMUM FORWARD VOLTAGE DROP, Pulsed	(I <sub>f</sub> = 7.5 Amps)			
	T <sub>J</sub> = 25 °C	$V_{f}$	0.56	Volts
	T <sub>J</sub> = 125 °C	- 1	0.51	
MAXIMUM REVERSE CURRENT (I <sub>r</sub> @ 45V PIV)				
	T <sub>J</sub> = 25 °C	I <sub>r</sub>	0.75	mA
	T <sub>.1</sub> = 125 °C		35	

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## **MECHANICAL DIMENSIONS: In Inches / mm**



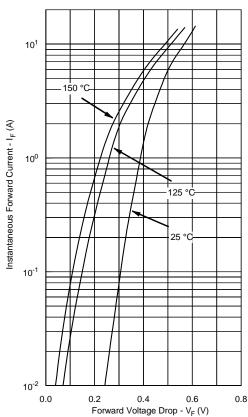


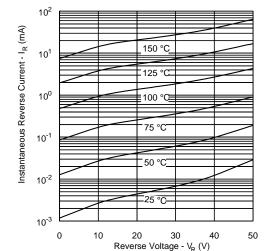
SHD-1

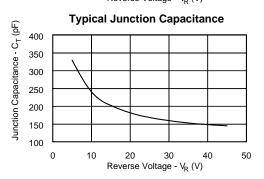
SHD-1B

**Typical Reverse Characteristics** 











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